SENTECH Erfolg durch Leistung

Berlin, 9/17/2019

Aktuelles Experiment:
noname.rcp

Modellbeschreibung

Number	Layer Name	Thickness [nm]	Refr. Index [632.8 nm]	Fitted
0	Air	-	1.000	no
1	NoName0	36.80	1.528	yes
2	Silicon DUV-NIR	-	3.874	no

Fit parameter

Fit parameter	Fit result
[1,1] NoName0: Thickness [nm]	36.80
NoName0: N0	1.518

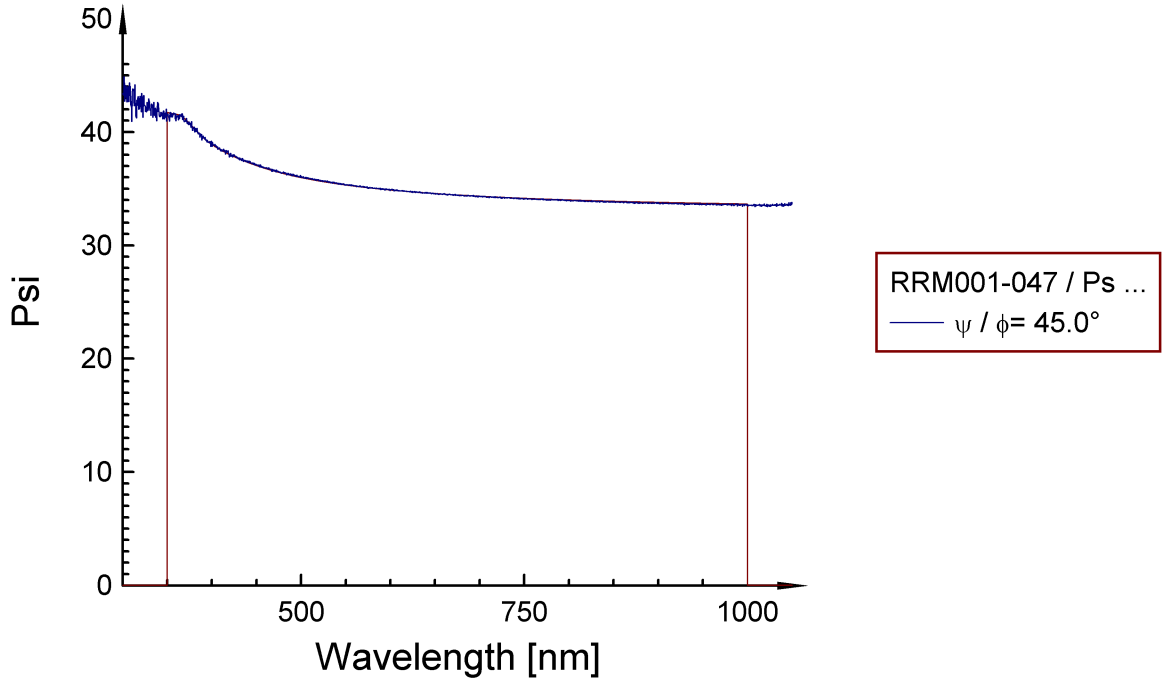
All parameter

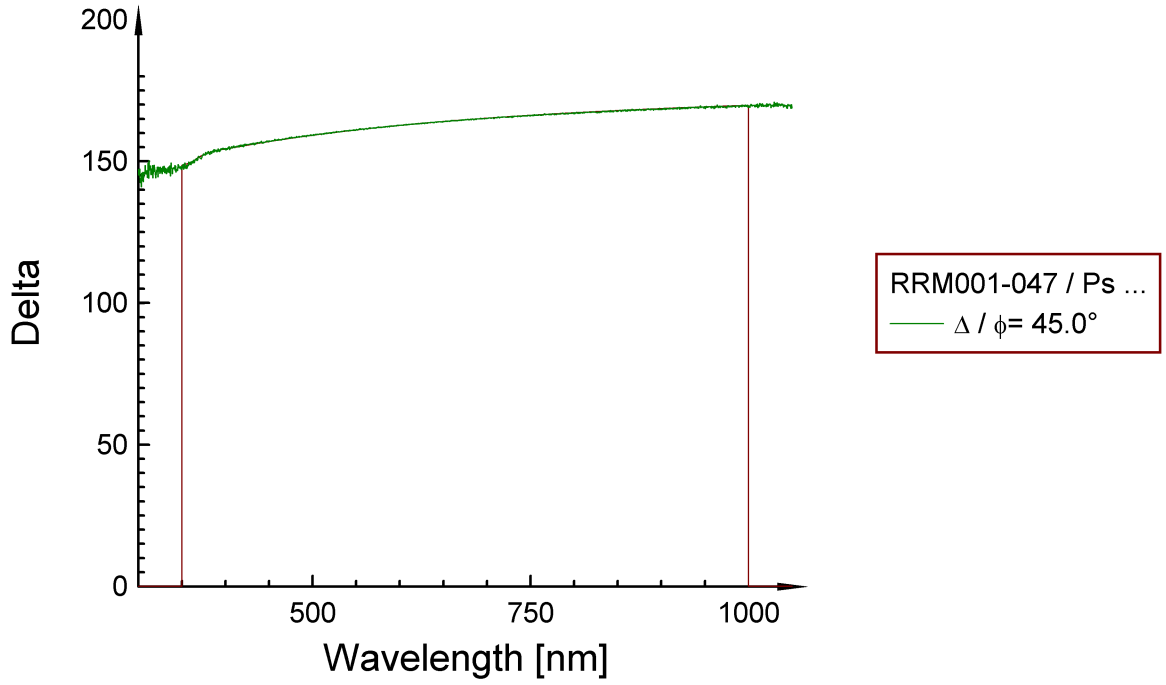
Parameter	Value
[1] Wavelength [nm]	632.8
[1] Angle [°]	70.00
[1] Time [s]	0.0
[1] Temperature [°C]	23.5
[1] Sample rotation [°]	0.00
[1] Depol. D0	1.0000
[1] Depol. D1	0.0000
[1] Depol. D2	0.0000
[1] Beam diameter	4.00
[1] Aperture diameter	4.00
[1,1] Thickness variation	10.0
[1] Wavelength resolution (nm)	0.0
[1] Angle variation	3.0
[1] Angle offset [°]	0.00
[1] Wavelength Offset (nm)	0.00
[1] Wavelength Linear	1.00000
[1] Fraction Overlayer	1.000
[1] Backside Factor	1.000
Air: Refr. index	1.000
Air: Absorption	0.000
Air: N Offset	0.00000

Air: K Offset	0.00000
[1,1] NoName0: Thickness [nm]	36.80
NoName0: N0	1.518
NoName0: N1	40.0
NoName0: N2	0.0
NoName0: K0	0.000
NoName0: K1	0.000
NoName0: K2	0.000
NoName0: N Offset	0.00000
NoName0: K Offset	0.00000
Silicon DUV-NIR: N Offset	0.00000
Silicon DUV-NIR: K Offset	0.00000
Pola.Pos.	45.00
Pola.Offs.	0.00
Ret.Axis	0.00
Ret.Phase	90.00
Eta	1.00000
Ana.Offs.	0.00
Ana.Offs.Lin.	0.00
Ana.Offs.Quadr.	0.00
Psi Offs.	0.00
Psi Lin.	0.00
Psi Quadr.	0.00
Delta Offs.	0.00
Delta Lin.	0.00
Delta Quadr.	0.00
MSE	0.19195553

Measured Data

RRM001-047 / Psi, Delta / Spectral range: 300.2 nm - 1050.0 nm / Angle of incidence: 45.00 ° / 9/17/2019 3:36:58 PM


Psi
50
40
30
20
10
0
500
750
1000
Wavelength [nm]
RRM001-047 / Ps ...
ψ / ϕ= 45.0°


Delta
200
150
100
50
0
500
750
1000
Wavelength [nm]
RRM001-047 / Ps ...
Δ / ϕ= 45.0°